

STRUCTURE OF A DEEP TRENCH-TYPE DRAM AND METHOD FOR MAKING THE SAME

ABSTRACT

5

A structure and a manufacture method of a DRAM device with deep trench capacitors are described. Each capacitor has a collar oxide layer with different height for electrical isolation and leakage reduction. Further, the DRAM device has strip-type active areas to improve some optical errors and thus reduce sufficiently the contact resistance of a buried strap film of a capacitor.

10